Product data sheet

1. General description

NPN low V_{CEsat} transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5620PA

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability
- AEC-Q101 qualified

3. Applications

- Loadswitch
- · Battery-driven devices
- Power management
- Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
Ic	collector current		-	-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	7	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 6 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	33	46	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		C
3	С	collector	Transparent top view DFN2020-3 (SOT1061)	BE sym021

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4620PA		plastic, leadless thermal enhanced ultra thin small outline package; 3 terminals; 1.3 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1061

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4620PA	A6

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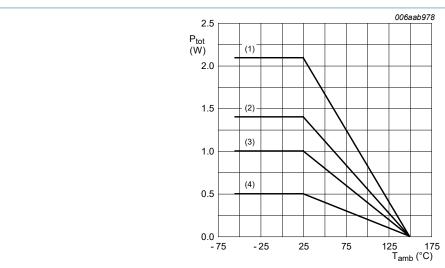
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	7	Α
I _B	base current			-	600	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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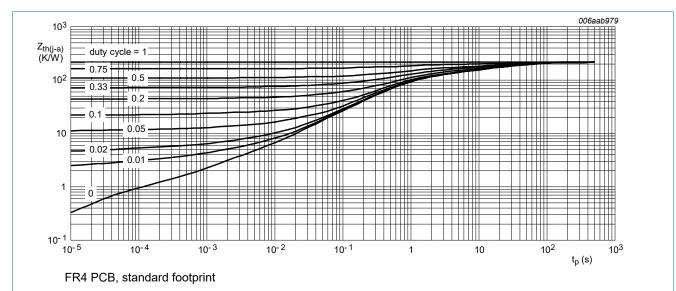
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9. Thermal characteristics

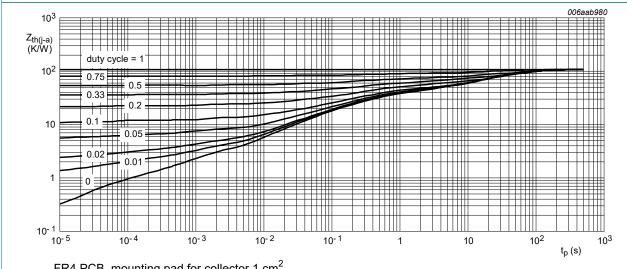
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	250	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	60	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [2]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



FR4 PCB, mounting pad for collector 1 cm²

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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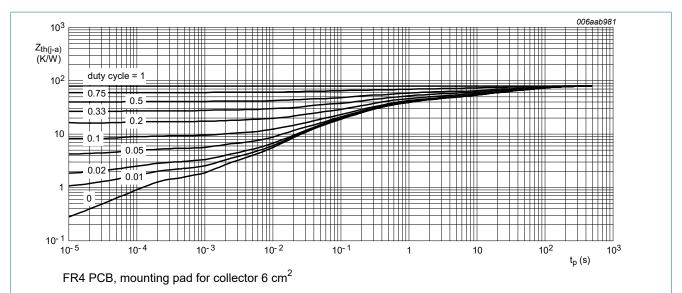


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

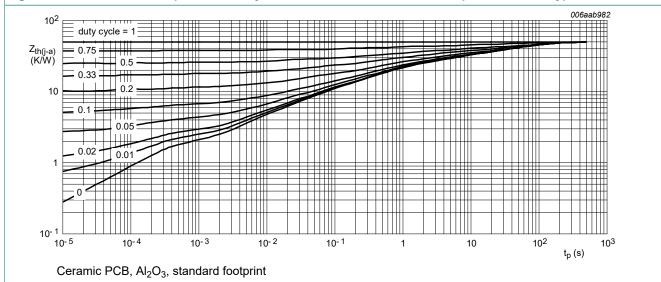


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

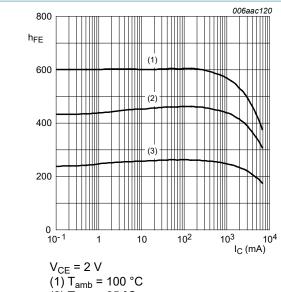
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10. Characteristics

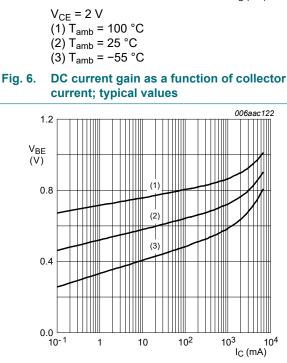
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
І _{сво}	collector-base cut-off	V _{CB} = 16 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 16 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 16 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	280	440	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	270	430	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	260	415	-	
		V_{CE} = 2 V; I_{C} = 6 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	330	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	20	30	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	37	55	mV
		I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	50	70	mV
		I_C = 2 A; I_B = 20 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	85	120	mV
		I_C = 3 A; I_B = 30 mA; pulsed; t_p ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	120	170	mV
		I_C = 4 A; I_B = 400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	135	185	mV
		$I_C = 6 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed}; t_p \le 200 \text{ mA}; \text{ pulsed}; t_p \ge 200 \text{ mA}; t$	-	200	275	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	33	46	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 10 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.9	V
		I_C = 6 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.97	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.74	0.9	V
d	delay time	$V_{CC} = 9 \text{ V; } I_{C} = 2 \text{ A; } I_{Bon} = 0.1 \text{ A;}$	-	25	-	ns
Г	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	55	-	ns
on	turn-on time		-	80	-	ns
·s	storage time		-	285	-	ns
f	fall time		-	50	-	ns
off	turn-off time		-	335	-	ns
Īτ	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	50	80	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	80	95	pF

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current; typical values

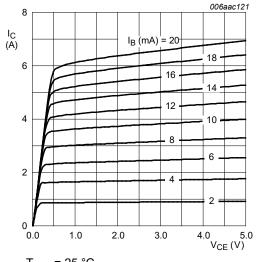


 $V_{CE} = 2 V$ (1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

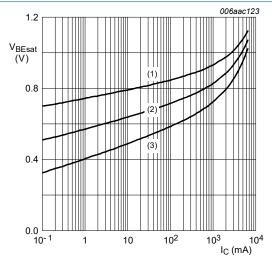
(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter voltage as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 7. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

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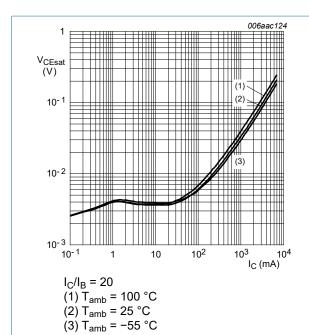


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

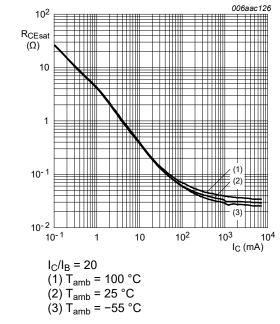


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

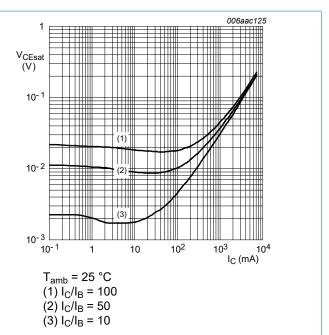


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

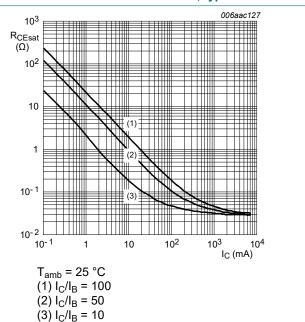
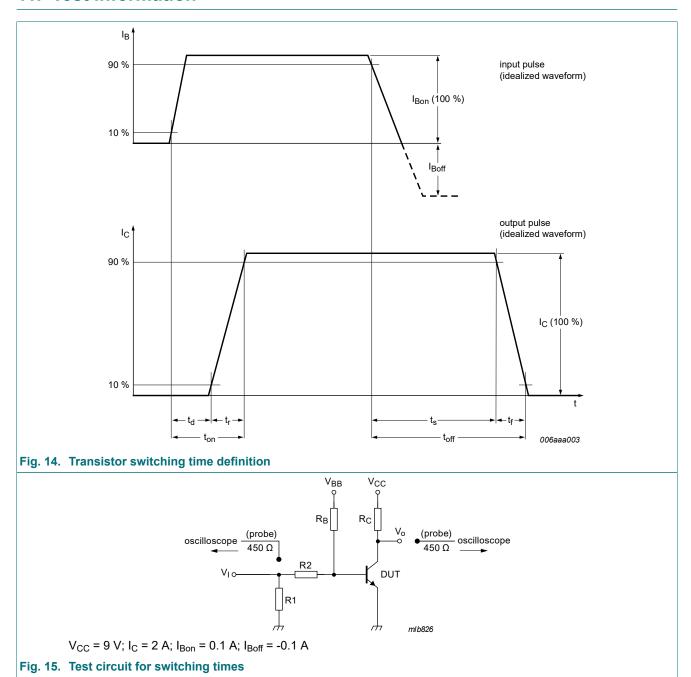


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



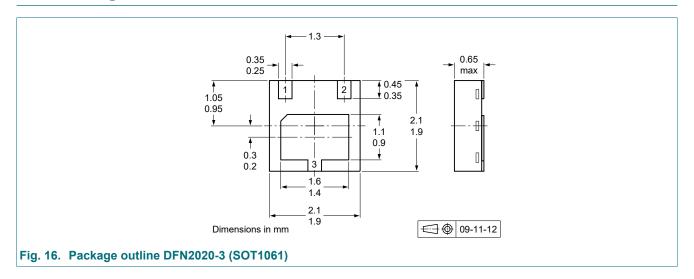
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

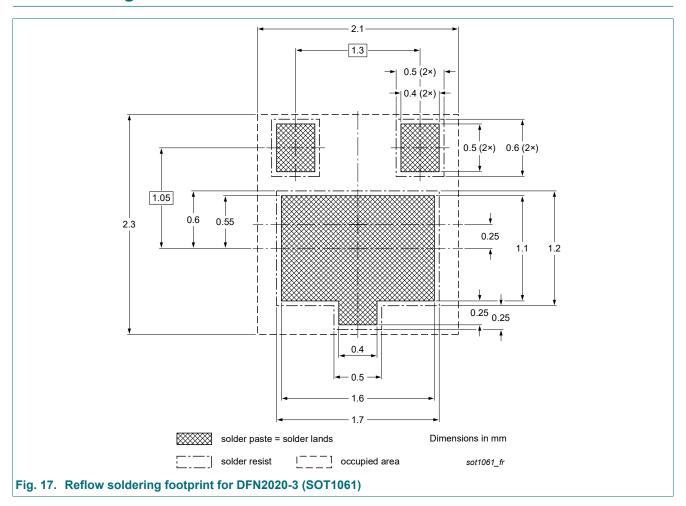
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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS4620PA v.2	20241018	Product data sheet	-	PBSS4620PA v.1			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed 						
PBSS4620PA v.1	20100518	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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